

N-channel 850 V, 0.2 Ω typ., 19 A MDmesh™ K5 Power MOSFET in a TO-247 package

Datasheet - production data

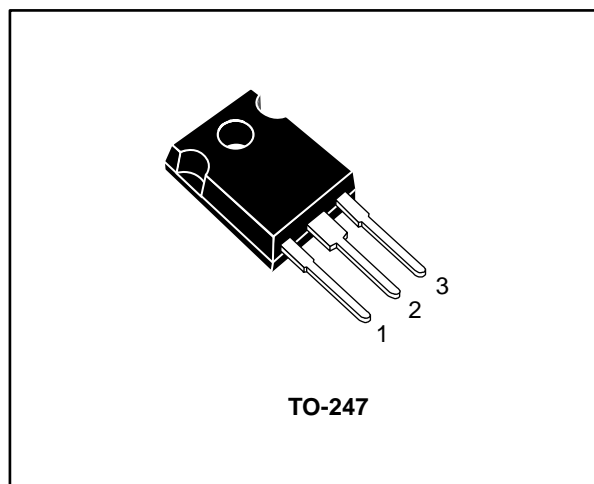
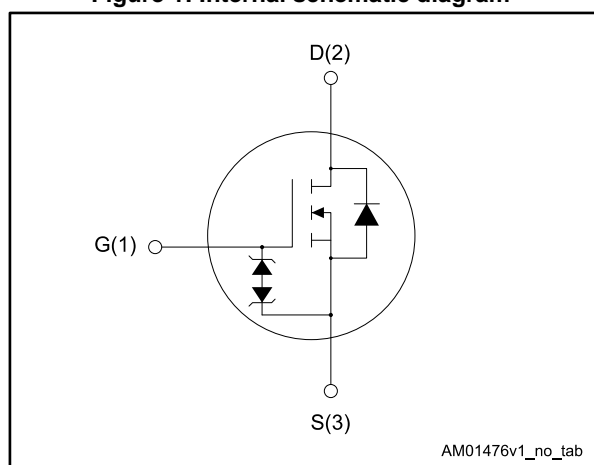


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D	P _{TOT}
STW23N85K5	850 V	0.275 Ω	19 A	250 W

- Industry's lowest R_{DS(on)} x area
- Industry's best figure of merit (FoM)
- Ultra low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This very high voltage N-channel Power MOSFET is designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1: Device summary

Order code	Marking	Package	Packing
STW23N85K5	23N85K5	TO-247	Tube

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at $T_{case} = 25\text{ °C}$	19	A
	Drain current (continuous) at $T_{case} = 100\text{ °C}$	12.4	
$I_{DM}^{(1)}$	Drain current (pulsed)	250	A
P_{TOT}	Total dissipation at $T_{case} = 25\text{ °C}$	250	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	6	V/ns
T_{stg}	Storage temperature	-55 to 150	°C
T_j	Operating junction temperature		

Notes:

⁽¹⁾ Pulse width is limited by safe operating area.

⁽²⁾ $I_{SD} \leq 19\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$; $V_{DS\text{ peak}} < V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.5	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient	45	

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
$I_{AR}^{(1)}$	Avalanche current, repetitive or not repetitive	6	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	200	mJ

Notes:

⁽¹⁾ Pulse width limited by T_{jmax} .

⁽²⁾ starting $T_j = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$.

2 Electrical characteristics

($T_{\text{case}} = 25\text{ °C}$ unless otherwise specified)

Table 5: Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	$V_{\text{GS}} = 0\text{ V}$, $I_{\text{D}} = 1\text{ mA}$	850			V
I_{DSS}	Zero gate voltage drain current	$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 850\text{ V}$			10	μA
		$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 850\text{ V}$, $T_{\text{case}} = 125\text{ °C}$			50	
I_{GSS}	Gate-body leakage current	$V_{\text{DS}} = 0\text{ V}$, $V_{\text{GS}} = \pm 20\text{ V}$			± 10	μA
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{DS}} = V_{\text{GS}}$, $I_{\text{D}} = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{\text{DS(on)}}$	Static drain-source on-resistance	$V_{\text{GS}} = 10\text{ V}$, $I_{\text{D}} = 9.5\text{ A}$		0.2	0.275	Ω

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{\text{DS}} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{\text{GS}} = 0\text{ V}$	-	1650	-	pF
C_{oss}	Output capacitance		-	115	-	
C_{rss}	Reverse transfer capacitance		-	2	-	
$C_{\text{oss eq.}}^{(1)}$	Equivalent output capacitance	$V_{\text{DS}} = 0\text{ to }680\text{ V}$, $V_{\text{GS}} = 0\text{ V}$	-	185	-	pF
R_{G}	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_{\text{D}} = 0\text{ A}$	-	3.5	-	Ω
Q_{g}	Total gate charge	$V_{\text{DD}} = 520\text{ V}$, $I_{\text{D}} = 60\text{ A}$, $V_{\text{GS}} = 10\text{ V}$ (see Figure 17 : "Gate charge test circuit")	-	38	-	nC
Q_{gs}	Gate-source charge		-	11	-	
Q_{gd}	Gate-drain charge		-	20	-	

Notes:

⁽¹⁾ $C_{\text{oss eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{\text{d(on)}}$	Turn-on delay time	$V_{\text{DD}} = 400\text{ V}$, $I_{\text{D}} = 9.5\text{ A}$ $R_{\text{G}} = 4.7\text{ }\Omega$, $V_{\text{GS}} = 10\text{ V}$ (see Figure 16 : "Switching times test circuit for resistive load" and Figure 21 : "Switching time waveform")	-	22	-	ns
t_{r}	Rise time		-	14	-	
$t_{\text{d(off)}}$	Turn-off delay time		-	55	-	
t_{f}	Fall time		-	8	-	

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		19	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		76	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 19\text{ A}$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 19\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 18 : "Test circuit for inductive load switching and diode recovery times")	-	510		ns
Q_{rr}	Reverse recovery charge		-	11		μC
I_{RRM}	Reverse recovery current		-	43		A
t_{rr}	Reverse recovery time	$I_{SD} = 19\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 18 : "Test circuit for inductive load switching and diode recovery times")	-	684		ns
Q_{rr}	Reverse recovery charge		-	14		μC
I_{RRM}	Reverse recovery current		-	41		A

Notes:

(1) Pulse width is limited by safe operating area.

(2) Pulse test: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

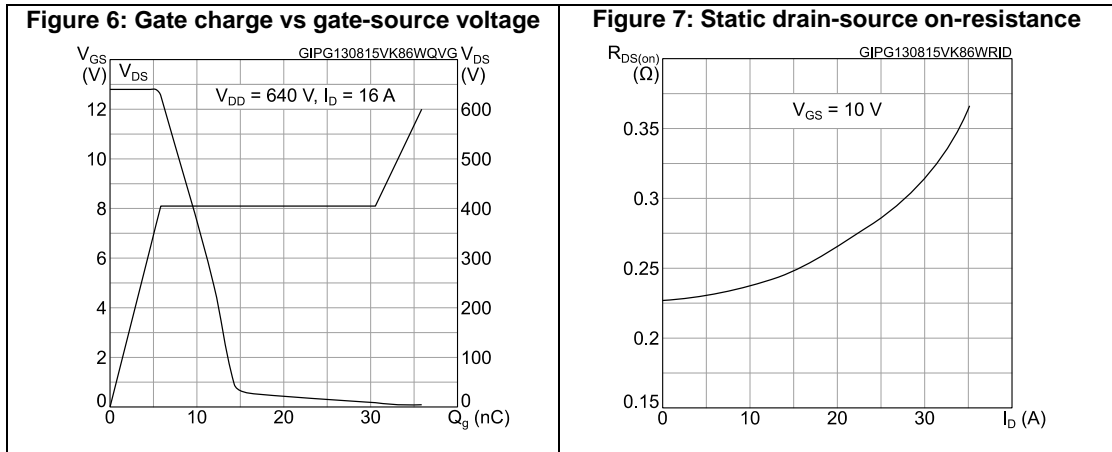
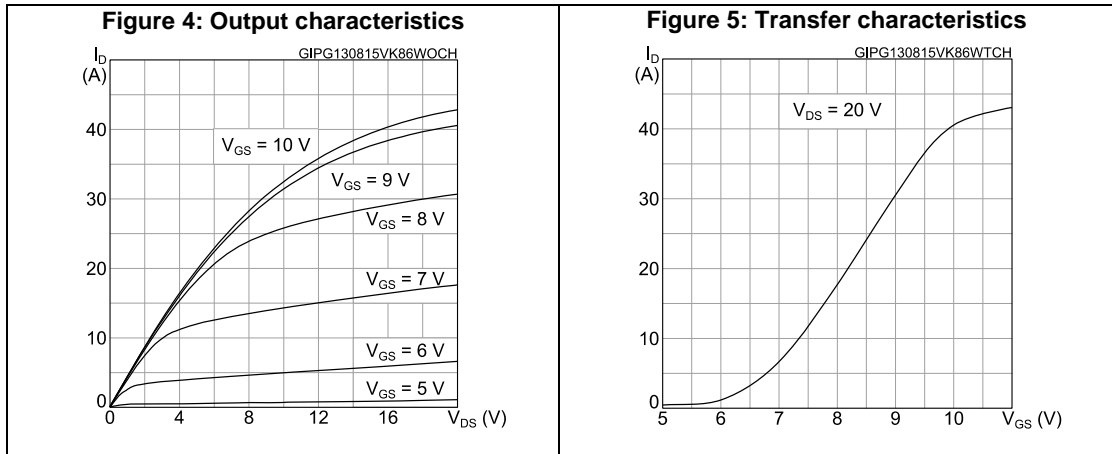
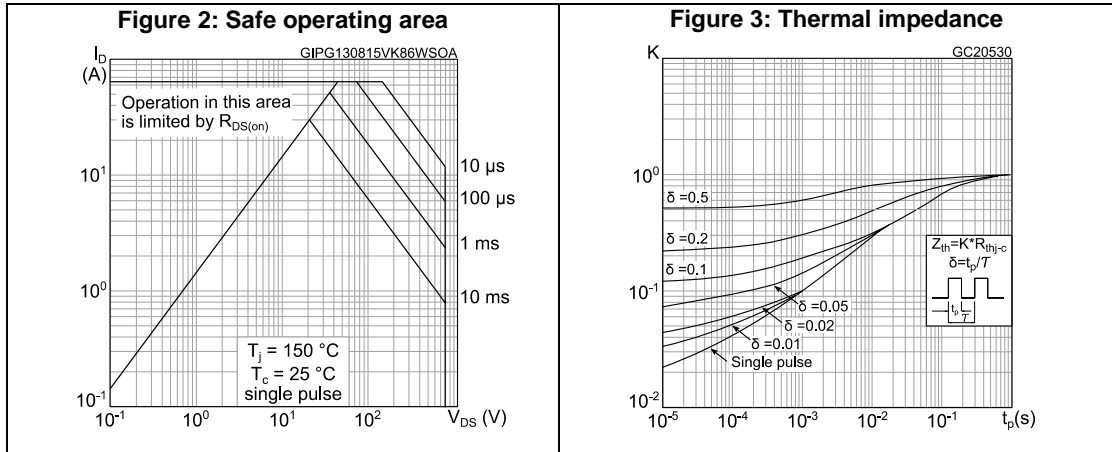


Figure 8: Capacitance variations

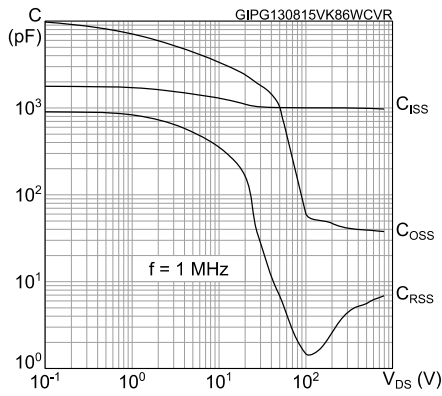


Figure 9: Normalized gate threshold voltage vs temperature

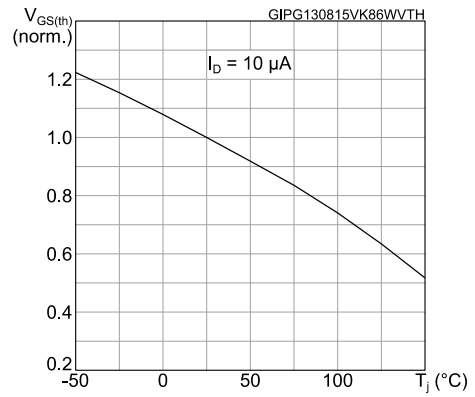


Figure 10: Normalized on-resistance vs temperature

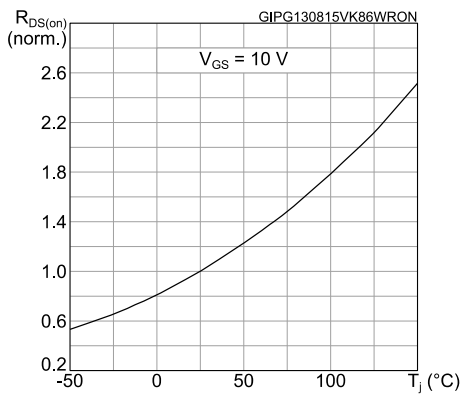


Figure 11: Normalized V(BR)DSS vs temperature

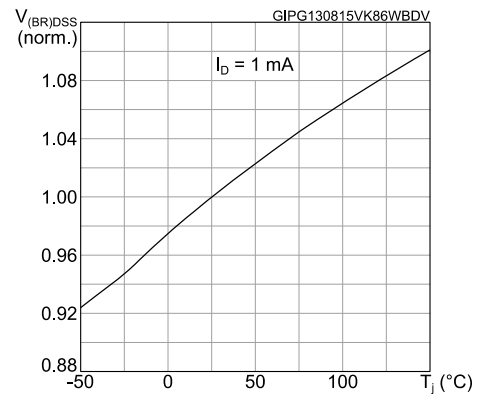


Figure 12: Output capacitance stored energy

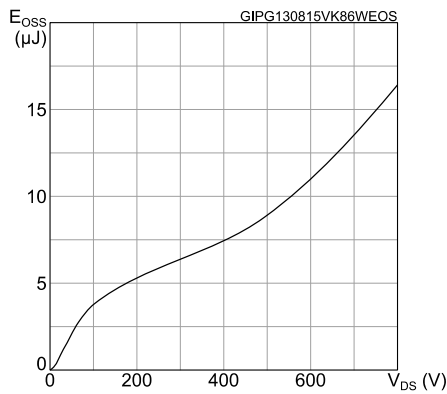


Figure 13: Source- drain diode forward characteristics

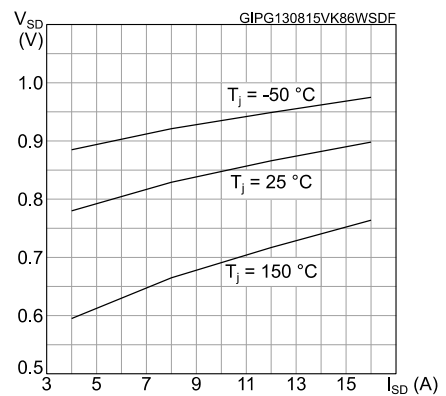


Figure 14: Maximum avalanche energy vs temperature (ID = 3.5 A)

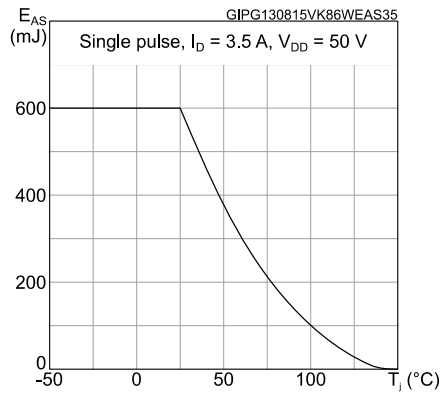
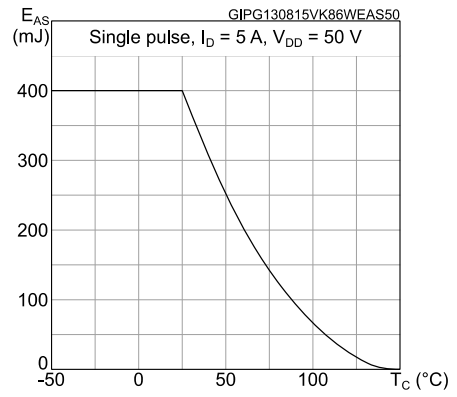
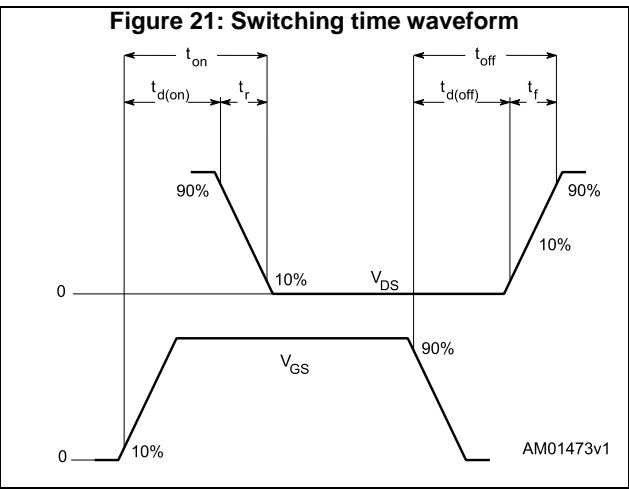
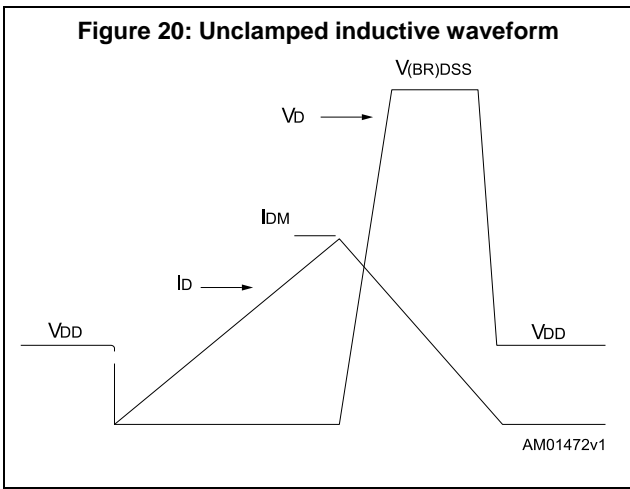
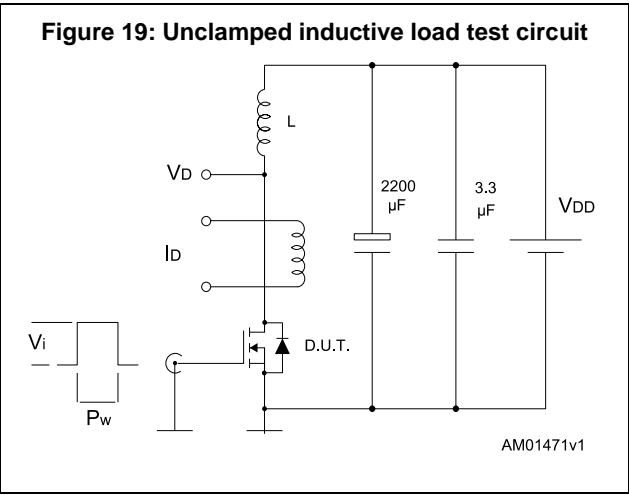
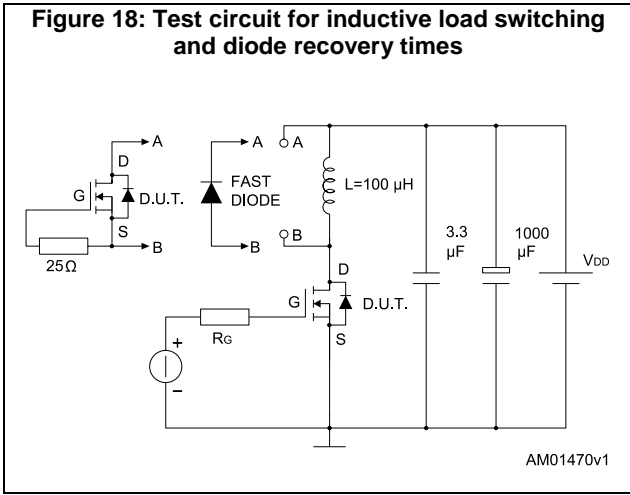
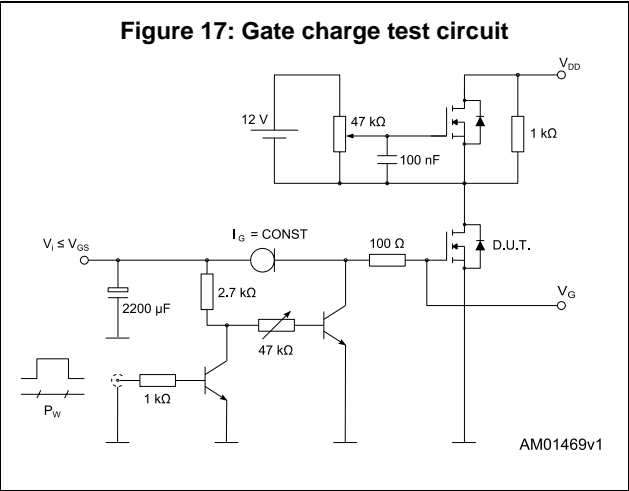
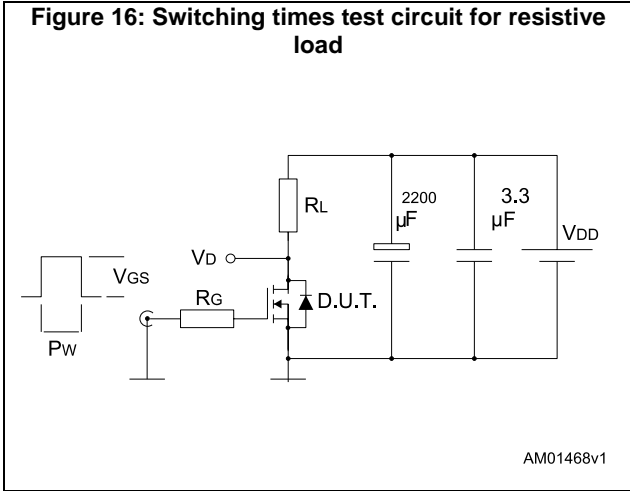


Figure 15: Maximum avalanche energy vs temperature (ID = 5.0 A)



3 Test circuits



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 TO-247 package information

Figure 22: TO-247 package outline

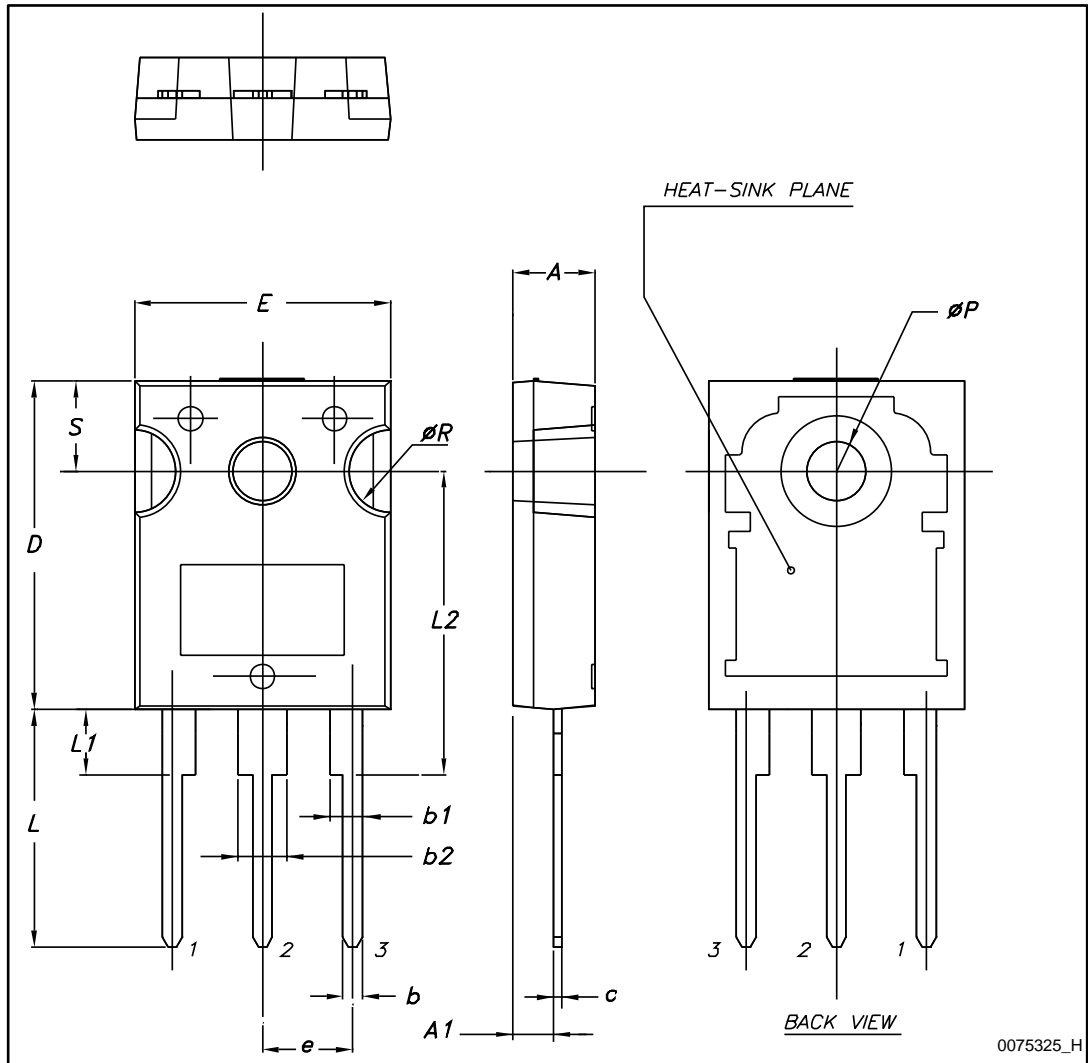


Table 9: TO-247 package mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
06-Aug-2012	1	First release.
21-Jan-2014	2	Document status promoted from preliminary to production data. Added Figure 12: Maximum avalanche energy vs temperature.
13-Aug-2015	3	Text and formatting changes throughout document. On cover page: - updated <i>Title, Features and Description</i> Updated Section <i>Electrical characteristics</i> Updated Section <i>Electrical characteristics (curves)</i> Updated and renamed Section <i>Package information</i> (was Package mechanical data)

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